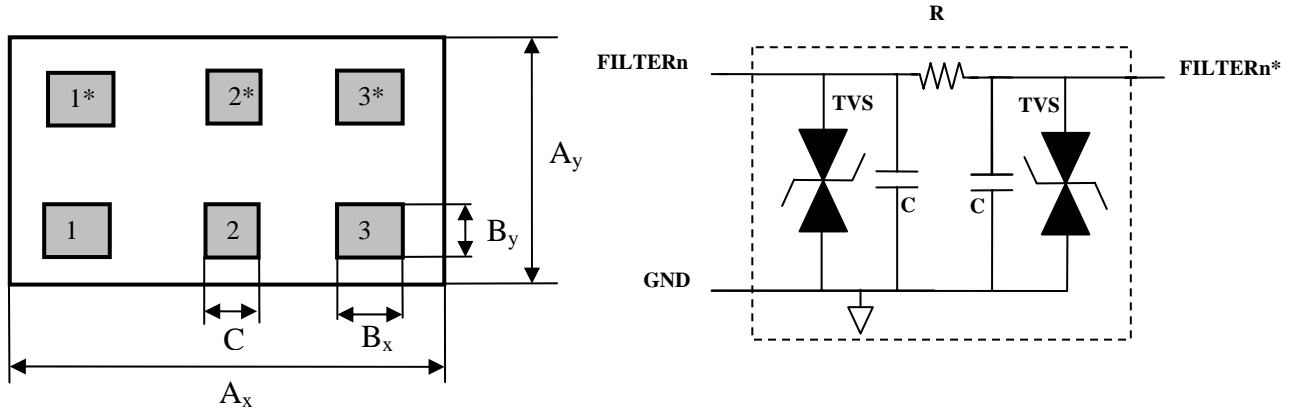


EMI-602M2

2 Channel EMI/RFI Filter Array with ESD Protection for Microphone Ports.



Mechanical date: $A_x = 800\mu\text{m}$, $A_y = 470\mu\text{m}$.
 $B_x = 120\mu\text{m}$, $B_y = 97\mu\text{m}$
 $C_x = C_y = 103\mu\text{m}$

Schematic and pinning diagram.

Chip thickness: $138 \pm 12\mu\text{m}$.

Scribe Line width - $60\mu\text{m}$.

Top Metal: Al – for wire bonding.

Back side: Ti-Ni-Ag for soldering.

Pin 2&2*-GND

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	V_{RWM}	-	5	V
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4	± 10 (Contact); ± 16 (Air).	kV
Max. junction temperature	T_J	-	125	$^{\circ}\text{C}$

Characteristics ($T_j = 25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	Breakdown voltage	$I_R = 1\text{mA}$	6,02	-	9,0	V
I_R	Diode reverse leakage current	$V = 5\text{V}$	-	-	4	μA
V_f	Diode Forward Voltage	$I_f = 10\text{mA}$	-	0.8	1.0	V
R	Resistance	-	27	32	37	Ohm
C_{in}	Capacitance	$V_R = 2.5\text{V}$, $f = 1\text{MHz}$			160	pF

*- For Device testing.